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(54) Title: DEPOSITION REACTOR WITH PLASMA SOURCE

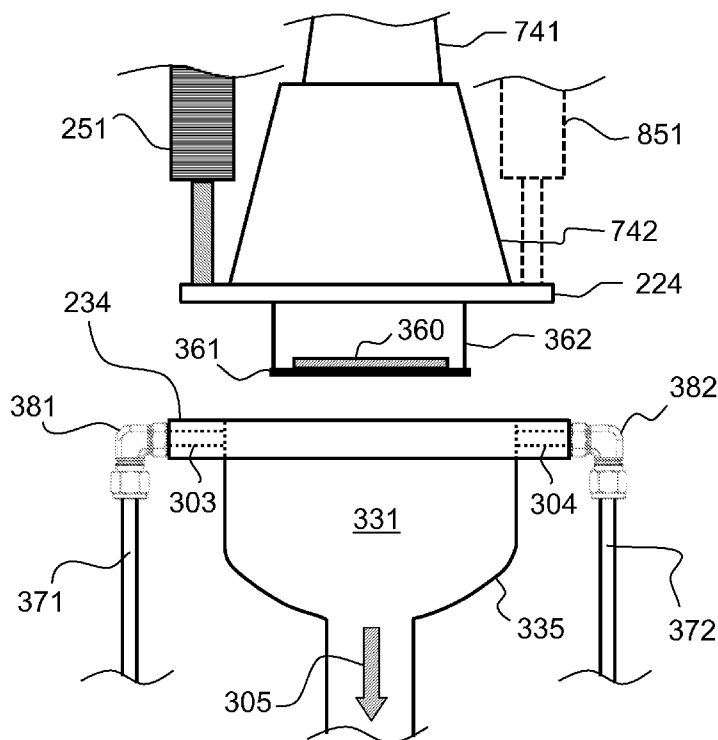


Fig. 10

(57) Abstract: The invention relates to a deposition reactor including an in-feed part that defines an expansion space which is configured to lead reactants as a top to bottom flow from a plasma source (110) towards a reaction chamber, the expansion space widening towards the reaction chamber (335), and a lifting mechanism for loading at least one substrate (360) to the reaction chamber from the top side of the reaction chamber. The deposition reactor is configured to deposit material on said at least one substrate in the reaction chamber by sequential self-saturating surface reactions.



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